

40V NPN SMALL SIGNAL TRANSISTOR IN X1-DFN1006-3

Features

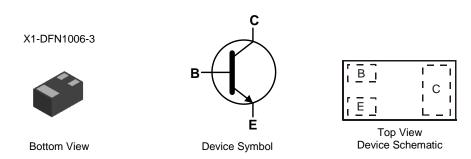
- BV_{CEO} > 40V
- I_C = 200mA High Collector Current
- P_D = 1000mW Power Dissipation
- 0.60mm² Package Footprint, 13 Times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary PNP Type MMBT3906LP
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

 This part is qualified to JEDEC standards (as references in AEC-Q101) for High Reliability. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020 Terminals: Finish — NiPdAu, Solderable per MIL-STD-202, Method 208 4
- Weight: 0.0008 grams (Approximate)



Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMBT3904LP-7	1N	7	8mm	3,000
MMBT3904LP-7B	1N	7	8mm	10,000
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

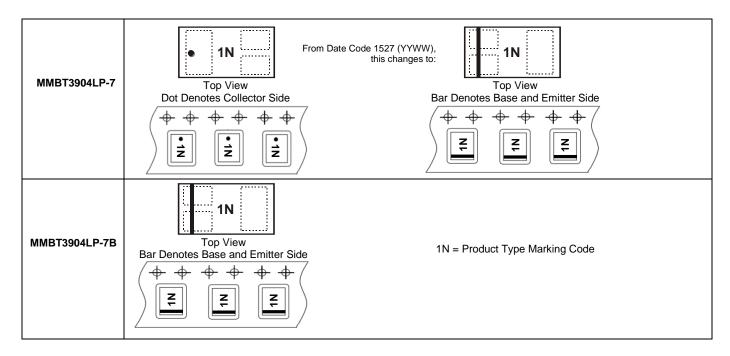
No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	lc	200	mA
Peak Collector Current	I _{CM}	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	Р	400	mW	
	(Note 6)	- P _D	1000	TTIVV	
Thermal Desistance, lunction to Archient	(Note 5)		310	- °C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	120		
Thermal Resistance, Junction to Lead (Note 7)		R _{θJL}	120	°C/W	
Operating and Storage and Temperature Ran	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes: 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.

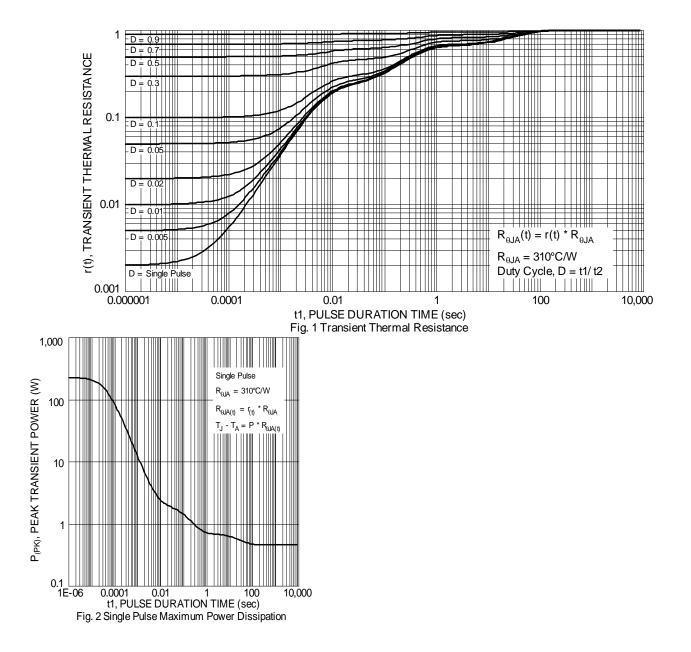
6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.

7. Thermal resistance from junction to solder-point (on the exposed collector pad).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics





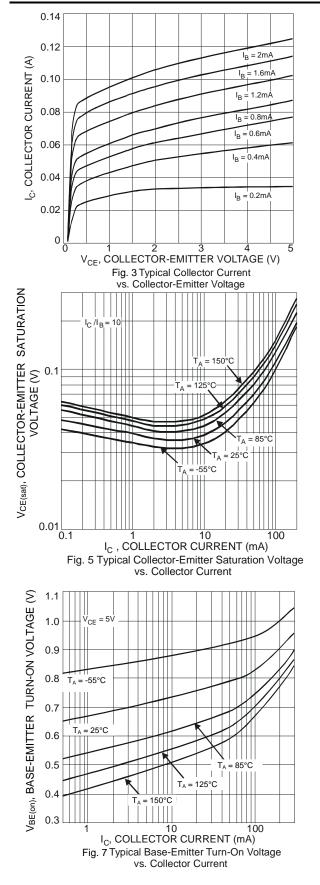
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

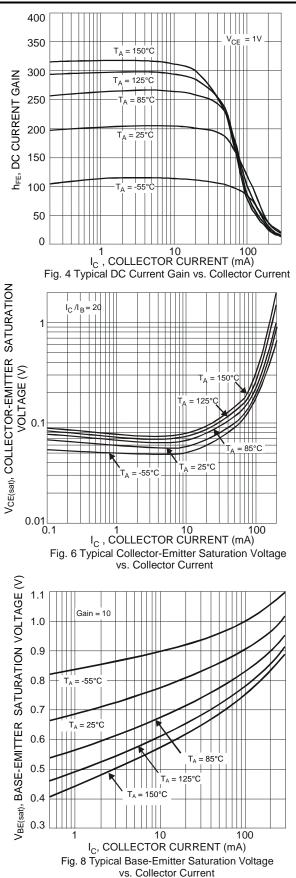
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV _{CBO}	60		V	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0 A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	40	_	V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0{\rm A}$
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0	_	V	$I_{E} = 10\mu A, I_{C} = 0A$
Collector Cutoff Current	ICEX	_	50	nA	$V_{CE} = 30V, V_{EB(off)} = 3.0V$
Base Cutoff Current	I _{BL}	_	50	nA	$V_{CE} = 30V, V_{EB(off)} = 3.0V$
ON CHARACTERISTICS (Note 9)					
		40			$I_{C} = 100 \mu A, V_{CE} = 1.0 V$
		70	_		$I_{C} = 1.0 \text{mA}, V_{CE} = 1.0 \text{V}$
DC Current Gain	h _{FE}	100	300	_	$I_{C} = 10 \text{mA}, V_{CE} = 1.0 \text{V}$
		60	_		$I_{C} = 50 \text{mA}, V_{CE} = 1.0 \text{V}$
		30	_		I _C = 100mA, V _{CE} = 1.0V
Collector Emitter Seturation Voltage			0.20	V	I _C = 10mA, I _B = 1.0mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	0.30		I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage		0.65	0.85	V	I _C = 10mA, I _B = 1.0mA
Dase-Elline Saturation Voltage	V _{BE(sat)}	_	0.95		$I_{\rm C} = 50 {\rm mA}, I_{\rm B} = 5.0 {\rm mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	Cobo	_	4.0	pF	$V_{CB} = 5.0V$, f = 1.0MHz, I _E = 0A
Input Capacitance	C _{ibo}		8.5	pF	$V_{EB} = 0.5V$, f = 1.0MHz, I _C = 0A
Input Impedance	h _{ie}	1.0	10	kΩ	
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h _{fe}	100	400		f = 1.0 kHz
Output Admittance	h _{oe}	1.0	40	μs	
Current Gain-Bandwidth Product	f _T	300	—	MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 100MHz
SWITCHING CHARACTERISTICS	•		•	•	·
Delay Time	t _d	_	35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Rise Time	tr		35	ns	$V_{BE(off)} = 0.5V, I_{B1} = 1.0mA$
Storage Time	ts	_	200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Fall Time	t _f	_	50	ns	$I_{B1} = -I_{B2} = 1.0 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

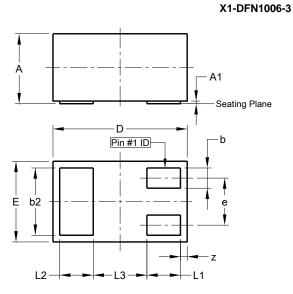






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



Х	X1-DFN1006-3				
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	1	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
z	0.02	0.08	0.05		
All Di	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Y –

Y1

G2 -



-⊢G1

- X1

Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70

X1-DFN1006-3



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